

MAC228A Series

Sensitive Gate Triacs

Silicon Bidirectional Thyristors

Designed primarily for industrial and consumer applications for full-wave control of AC loads such as appliance controls, heater controls, motor controls, and other power switching applications.

Features

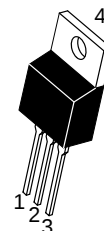
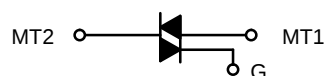
- Sensitive Gate Triggering in 3 Modes for AC Triggering on Sinking Current Sources
- Four Mode Triggering for Drive Circuits that Source Current
- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading
- These Devices are Pb-Free and are RoHS Compliant*



ON Semiconductor®

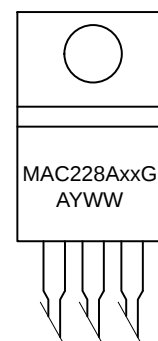
www.onsemi.com

TRIACS
8 AMPERES RMS
200 – 800 VOLTS



TO-220
CASE 221A
STYLE 4

MARKING DIAGRAM



xx = 4, 6, 8, or 10
A = Assembly Location (Optional)*
Y = Year
WW = Work Week
G = Pb-Free Package

* The Assembly Location code (A) is optional. In cases where the Assembly Location is stamped on the package the assembly code may be blank.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAC228A Series

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)	V _{DRM} , V _{RRM}	200 400 600 800	V
On-State RMS Current, (T _C = 80°C) – Full Cycle Sine Wave 50 to 60 Hz	I _{T(RMS)}	8.0	A
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _J = 110°C)	I _{TSM}	80	A
Circuit Fusing Considerations, (t = 8.3 ms)	I ² t	26	A ² s
Peak Gate Current, (t ≤ 2 μs, T _C = 80°C)	I _{GM}	±2.0	A
Peak Gate Voltage, (t ≤ 2 μs, T _C = 80°C)	V _{GM}	±10	V
Peak Gate Power, (t ≤ 2 μs, T _C = 80°C)	P _{GM}	20	W
Average Gate Power, (t ≤ 8.3 ms, T _C = 80°C)	P _{G(AV)}	0.5	W
Operating Junction Temperature Range	T _J	-40 to 110	°C
Storage Temperature Range	T _{stg}	-40 to 150	°C
Mounting Torque	–	8.0	in lb

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction-to-Case	R _{θJC}	2.0	°C/W
Thermal Resistance – Junction-to-Ambient	R _{θJA}	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T _L	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Peak Repetitive Blocking Current, (V _D = Rated V _{DRM} , V _{RRM} ; Gate Open) T _J = 25°C	I _{DRM} , I _{RRM}	–	–	10	μA
T _J = 110°C		–	–	2.0	mA

ON CHARACTERISTICS

Peak On-State Voltage, (I _{TM} = ±11 A Peak, Pulse Width ≤ 2 ms, Duty Cycle ≤ 2%)	V _{TM}	–	–	1.8	V
Gate Trigger Current (Continuous DC), (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+); MT2(+), G(–); MT2(–), G(–) MT2(–), G(+)	I _{GT}	–	–	5.0 10	mA
Gate Trigger Voltage (Continuous DC), (V _D = 12 V, R _L = 100 Ω) MT2(+), G(+); MT2(+), G(–); MT2(–), G(–) MT2(–), G(+)	V _{GT}	–	–	2.0 2.5	V
Gate Non-Trigger Voltage (Continuous DC), (V _D = 12 V, T _C = 110°C, R _L = 100 Ω) All Four Quadrants	V _{GD}	0.2	–	–	V
Holding Current, (V _D = 12 Vdc, Initiating Current = ±200 mA, Gate Open)	I _H	–	–	15	mA
Gate-Controlled Turn-On Time, (V _D = Rated V _{DRM} , I _{TM} = 16 A Peak, I _G = 30 mA)	t _{gt}	–	1.5	–	μs

DYNAMIC CHARACTERISTICS

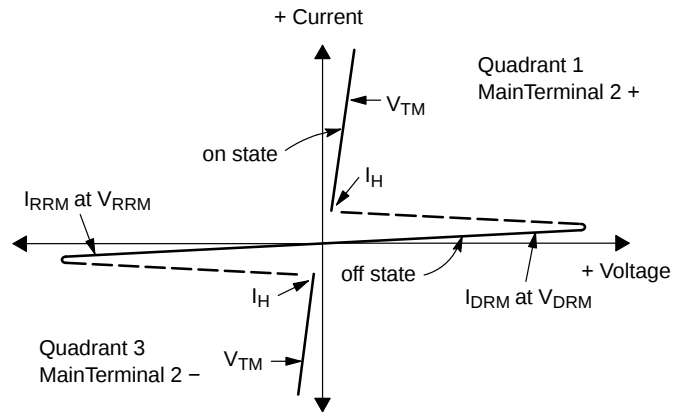
Critical Rate of Rise of Off-State Voltage, (V _D = Rated V _{DRM} , Exponential Waveform, T _C = 110°C)	dv/dt	–	25	–	V/μs
Critical Rate of Rise of Commutation Voltage, (V _D = Rated V _{DRM} , I _{TM} = 11.3 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, T _C = 80°C)	dv/dt(c)	–	5.0	–	V/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

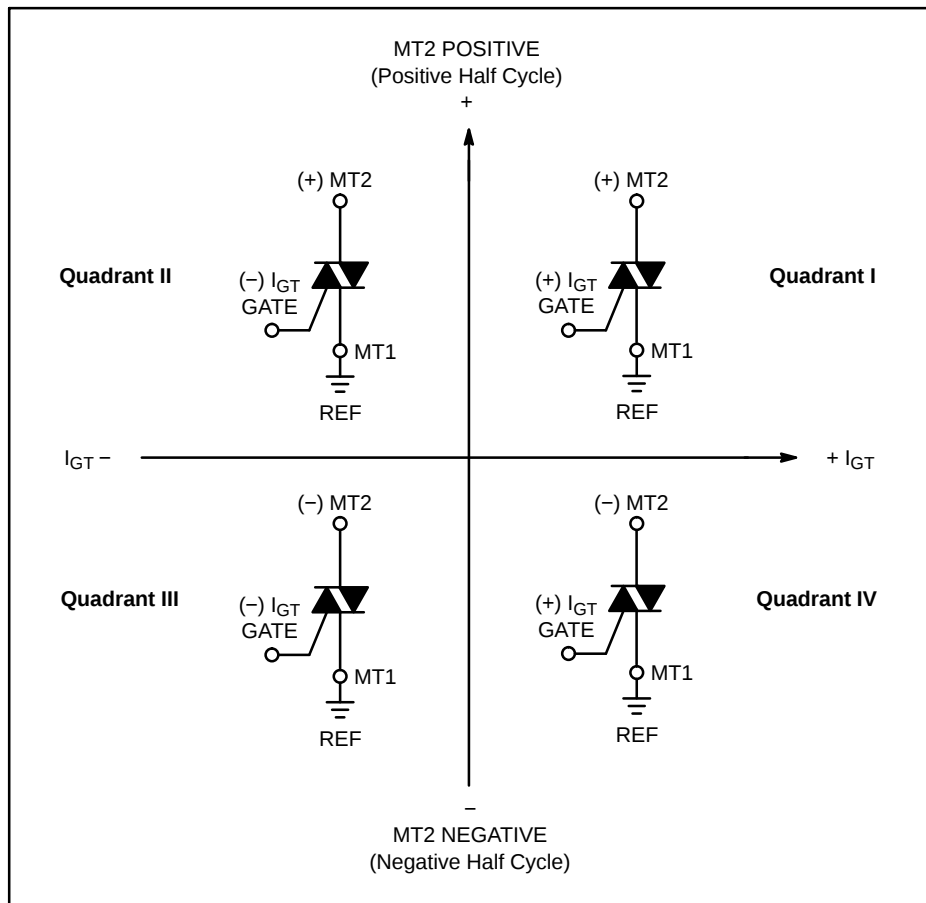
MAC228A Series

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

MAC228A Series

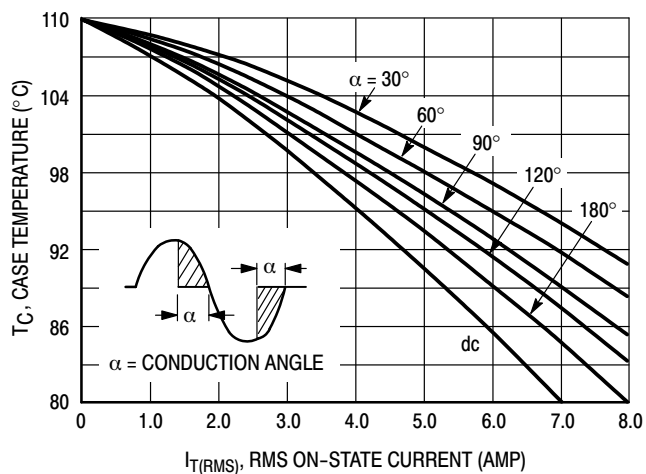


Figure 1. RMS Current Derating

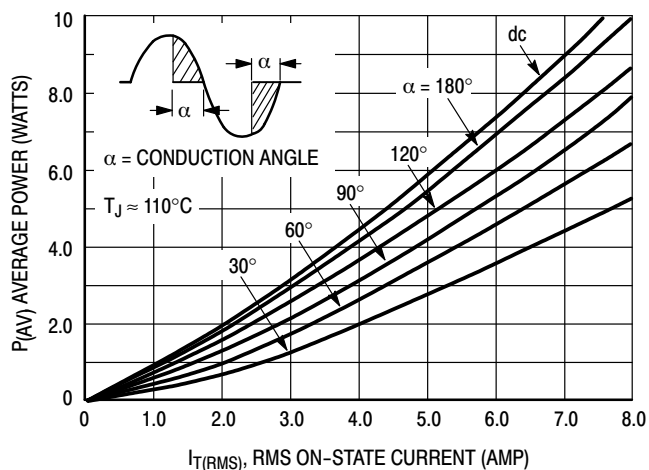


Figure 2. On-State Power Dissipation

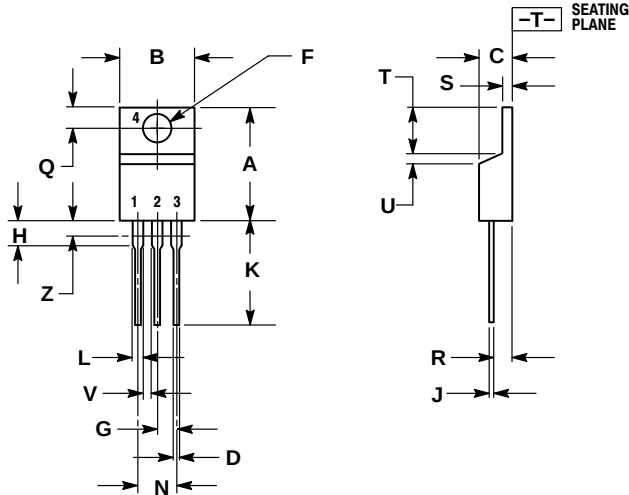
ORDERING INFORMATION

Device	Package	Shipping
MAC228A4G	TO-220 (Pb-Free)	500 Units / Bulk
MAC228A6G	TO-220 (Pb-Free)	500 Units / Bulk
MAC228A6TG	TO-220 (Pb-Free)	50 Units / Rail
MAC228A8G	TO-220 (Pb-Free)	500 Units / Bulk
MAC228A8TG	TO-220 (Pb-Free)	50 Units / Rail
MAC228A10G	TO-220 (Pb-Free)	500 Units / Bulk

MAC228A Series

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AH



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 4:

- PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. MAIN TERMINAL 2

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